

Silicon NPN Power Transistors

2SC4804

DESCRIPTION

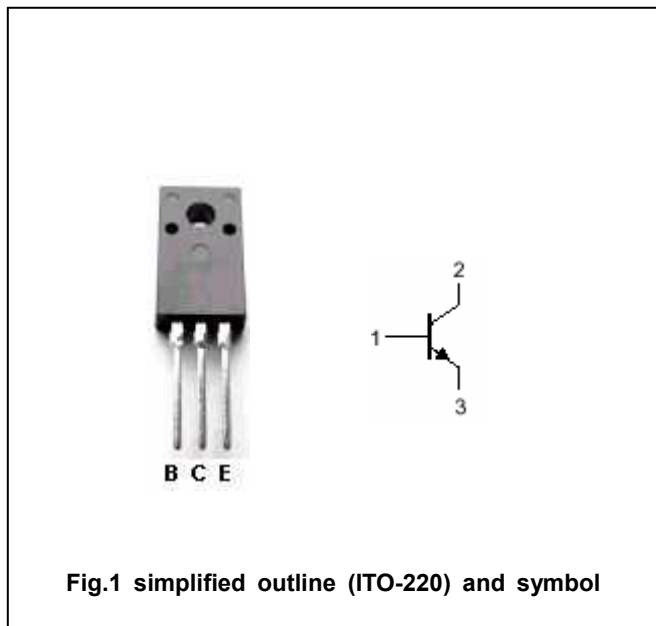
- With ITO-220 package
- High breakdown voltage

APPLICATIONS

- Switching regulator and high voltage switching applications
- High speed DC-DC converter applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	900	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		3	A
I_{CM}	Collector current-Peak		5	A
I_B	Base current		1	A
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	30	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

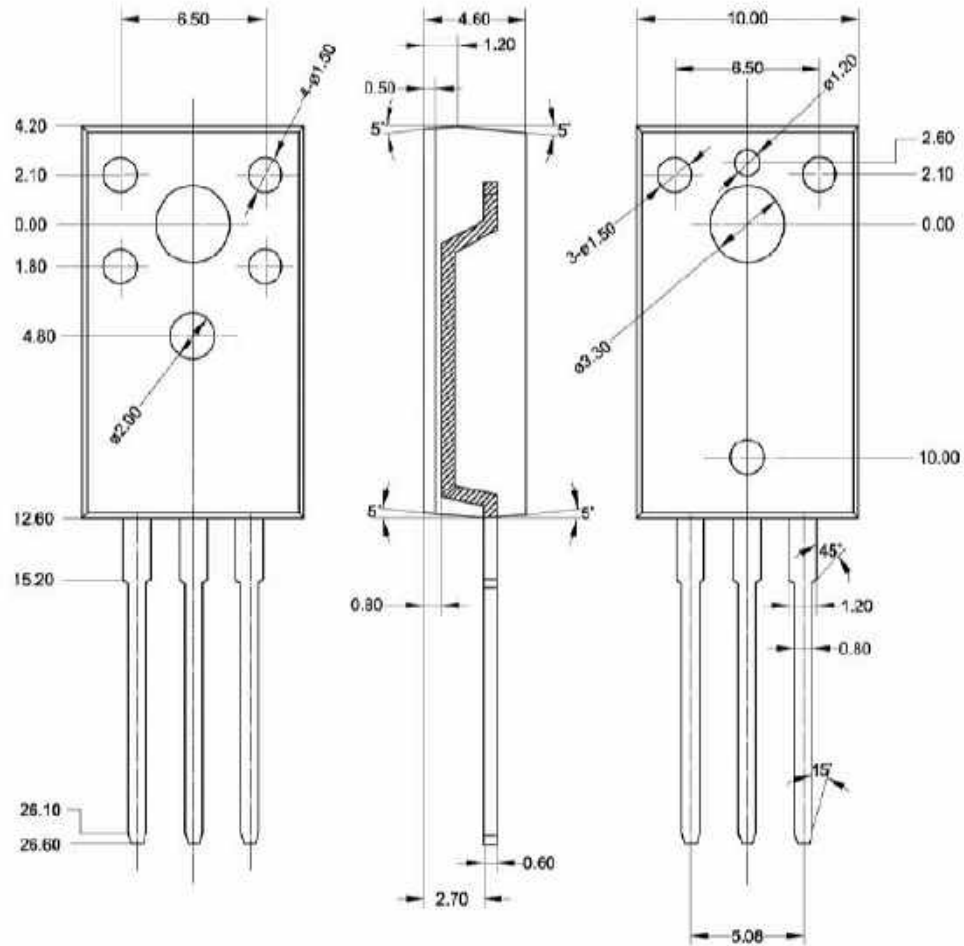
T_j=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	600			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	900			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =0.8A; I _B =0.16A			0.6	V
V _{BEsat}	Base-emitter saturation voltage	I _C =0.8A; I _B =0.16A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =0.8A ; V _{CE} =5V	10			

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PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.20 mm)